

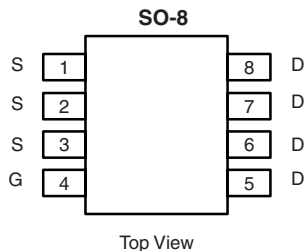
## N-Channel 30-V (D-S) MOSFET with Schottky Diode

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ )  | $I_D$ (A) |
|--------------|----------------------------|-----------|
| 30           | 0.0095 at $V_{GS} = 10$ V  | 13        |
|              | 0.0105 at $V_{GS} = 4.5$ V | 12        |

### SCHOTTKY PRODUCT SUMMARY

| $V_{DS}$ (V) | $V_{SD}$ (V)<br>Diode Forward Voltage | $I_F$ (A) |
|--------------|---------------------------------------|-----------|
| 30           | 0.53 V at 3.0 A                       | 3.0       |



**Ordering Information:** Si4736DY-T1-E3 (Lead (Pb)-free)  
Si4736DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

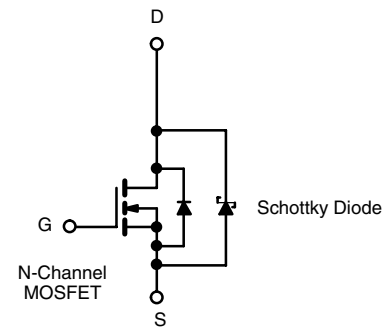
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- LITTLE FOOT® Plus Schottky
- Shoot-Thru-Free
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- DC/DC Converters Optimized for "Low-Side" Synchronous Rectifier Operation



### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter                                                       |                        | Symbol                            | 10 s        | Steady State | Unit |
|-----------------------------------------------------------------|------------------------|-----------------------------------|-------------|--------------|------|
| Drain-Source Voltage                                            |                        | V <sub>DS</sub>                   | 30          |              | V    |
| Gate-Source Voltage                                             |                        | V <sub>GS</sub>                   | ± 12        |              |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | T <sub>A</sub> = 25 °C | I <sub>D</sub>                    | 13          | 9            | A    |
|                                                                 | T <sub>A</sub> = 70 °C |                                   | 10          | 7            |      |
| Pulsed Drain Current                                            |                        | I <sub>DM</sub>                   | 50          |              |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup>       |                        | I <sub>S</sub>                    | 5           | 3.0          | W    |
| Maximum Power Dissipation <sup>a</sup>                          | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 3.1         | 1.40         |      |
|                                                                 | T <sub>A</sub> = 70 °C |                                   | 2.0         | 0.90         |      |
| Operating Junction and Storage Temperature Range                |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 |              | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                                | Symbol     | Typ. | Max. | Unit |
|------------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | 33   | 40   | °C/W |
|                                          |            | 70   | 85   |      |
| Maximum Junction-to-Foot (Drain)         | $R_{thJF}$ | 17   | 21   |      |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

This data sheet contains preliminary specifications that are subject to change.

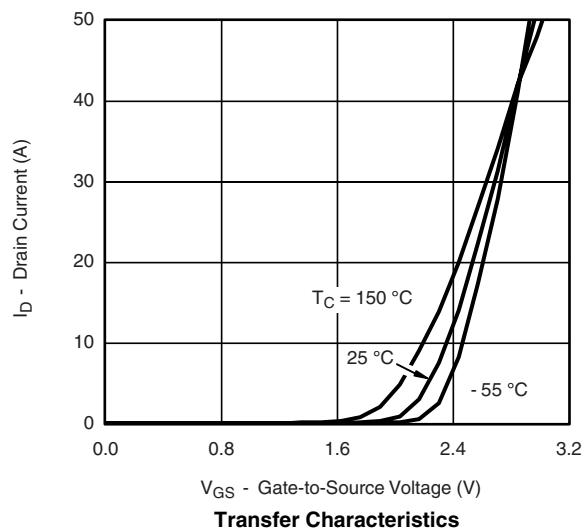
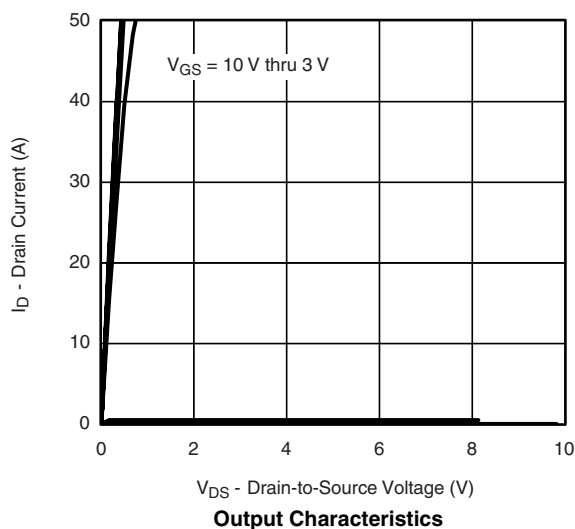
| MOSFET SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted |                     |                                                                                                                      |      |                   |        |      |
|----------------------------------------------------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------|------|-------------------|--------|------|
| Parameter                                                            | Symbol              | Test Conditions                                                                                                      | Min. | Typ. <sup>a</sup> | Max.   | Unit |
| Static                                                               |                     |                                                                                                                      |      |                   |        |      |
| Gate Threshold Voltage                                               | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                          | 0.8  | 1.35              | 1.9    | V    |
| Gate-Body Leakage                                                    | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V                                                                      |      |                   | ± 100  | nA   |
| Zero Gate Voltage Drain Current                                      | I <sub>DSS</sub>    | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                                                                        |      | 0.007             | 0.100  | mA   |
|                                                                      |                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 100 °C                                               |      | 1.5               | 10     |      |
|                                                                      |                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                               |      | 6.5               | 20     |      |
| On-State Drain Current <sup>b</sup>                                  | I <sub>D(on)</sub>  | V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V                                                                        | 20   |                   |        | A    |
| Drain-Source On-State Resistance <sup>b</sup>                        | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 13 A                                                                        |      | 0.0070            | 0.0095 | Ω    |
|                                                                      |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12 A                                                                       |      | 0.0083            | 0.0105 |      |
| Forward Transconductance <sup>b</sup>                                | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 13 A                                                                        |      | 56                |        | S    |
| Diode Forward Voltage <sup>b</sup>                                   | V <sub>SD</sub>     | I <sub>S</sub> = 3.0 A, V <sub>GS</sub> = 0 V                                                                        |      | 0.495             | 0.53   | V    |
|                                                                      |                     | I <sub>S</sub> = 3.0 A, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                               |      | 0.430             | 0.47   |      |
| Dynamic <sup>a</sup>                                                 |                     |                                                                                                                      |      |                   |        |      |
| Total Gate Charge                                                    | Q <sub>g</sub>      | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 13 A                                               |      | 37                | 55     | nC   |
| Gate-Source Charge                                                   | Q <sub>gs</sub>     |                                                                                                                      |      | 10                |        |      |
| Gate-Drain Charge                                                    | Q <sub>gd</sub>     |                                                                                                                      |      | 8.8               |        |      |
| Gate Resistance                                                      | R <sub>g</sub>      |                                                                                                                      |      | 0.8               |        | Ω    |
| Turn-On Delay Time                                                   | t <sub>d(on)</sub>  | V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω<br>I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω |      | 17                | 26     | ns   |
| Rise Time                                                            | t <sub>r</sub>      |                                                                                                                      |      | 14                | 21     |      |
| Turn-Off Delay Time                                                  | t <sub>d(off)</sub> |                                                                                                                      |      | 102               | 155    |      |
| Fall Time                                                            | t <sub>f</sub>      |                                                                                                                      |      | 26                | 40     |      |
| Source-Drain Reverse Recovery Time                                   | t <sub>rr</sub>     | I <sub>F</sub> = 3.0 A, dI/dt = 100 A/μs                                                                             |      | 42                | 65     |      |

Notes:

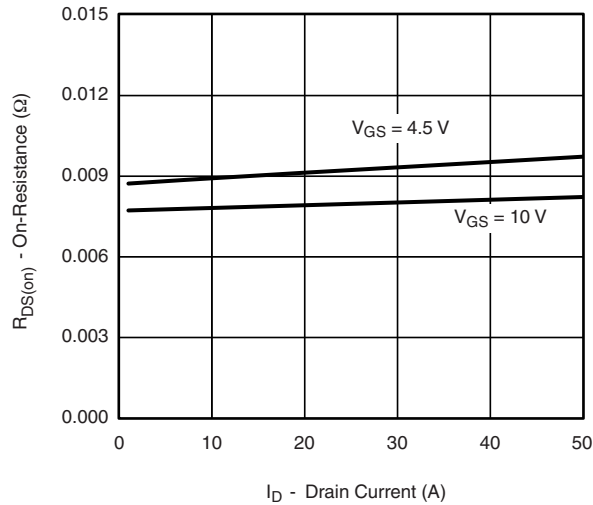
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

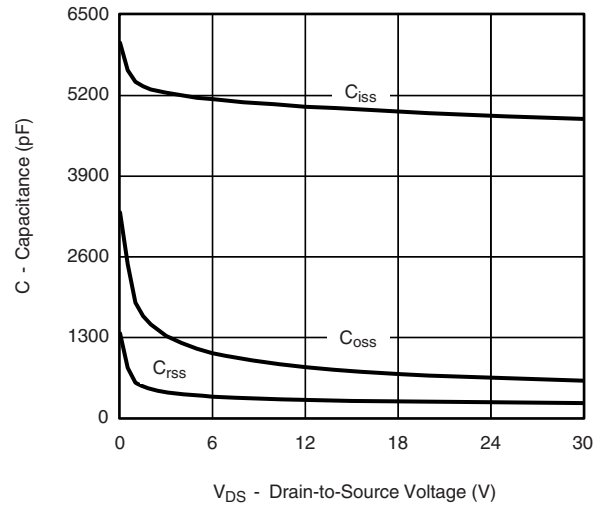
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25^\circ\text{C}$  unless otherwise noted

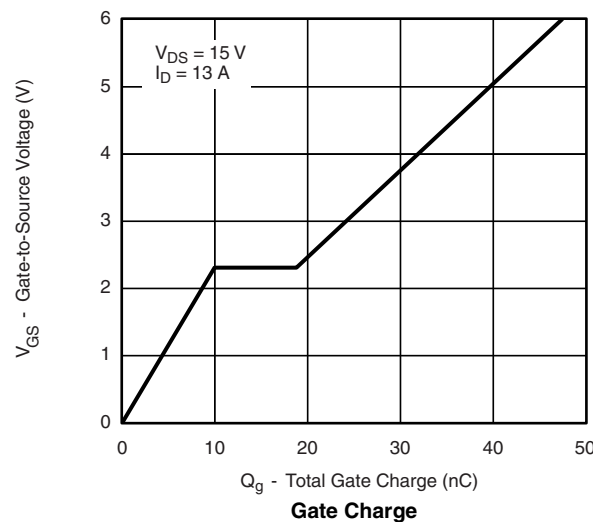
## TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



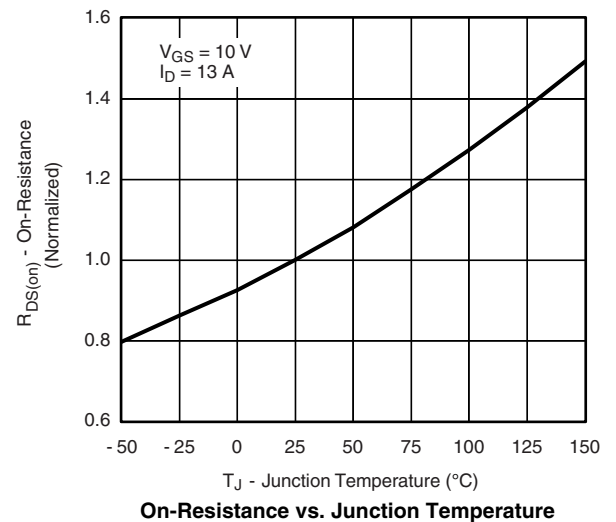
On-Resistance vs. Drain Current



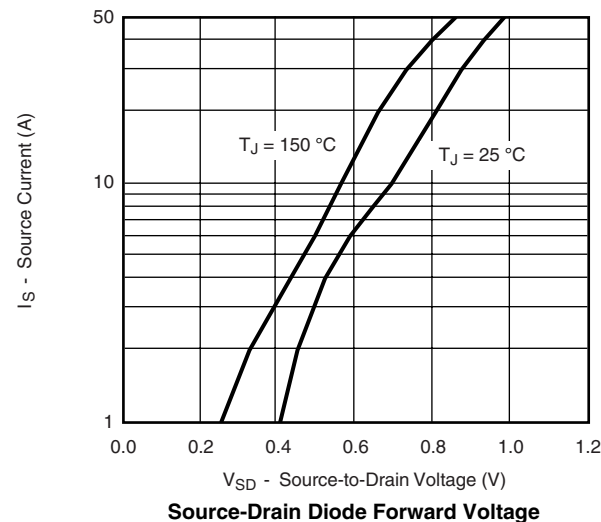
Capacitance



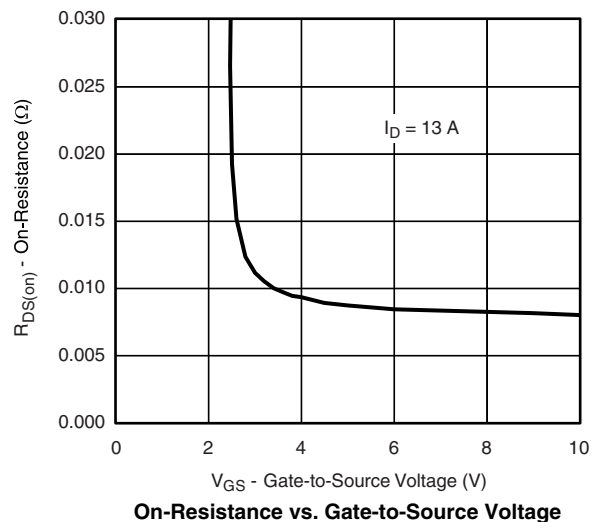
Gate Charge



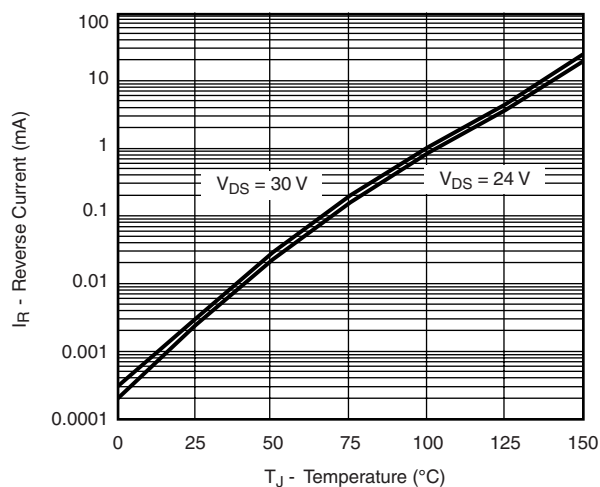
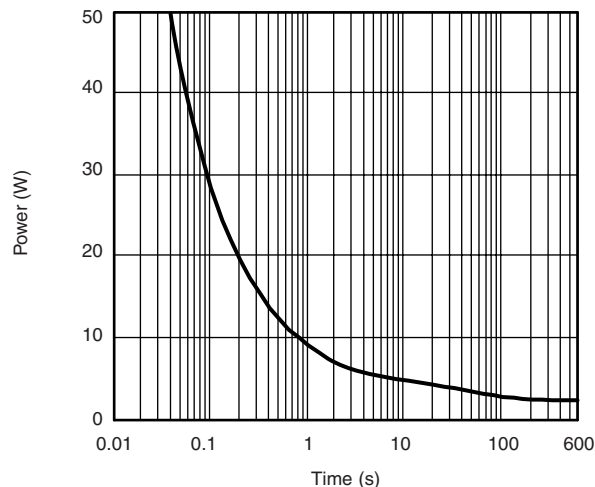
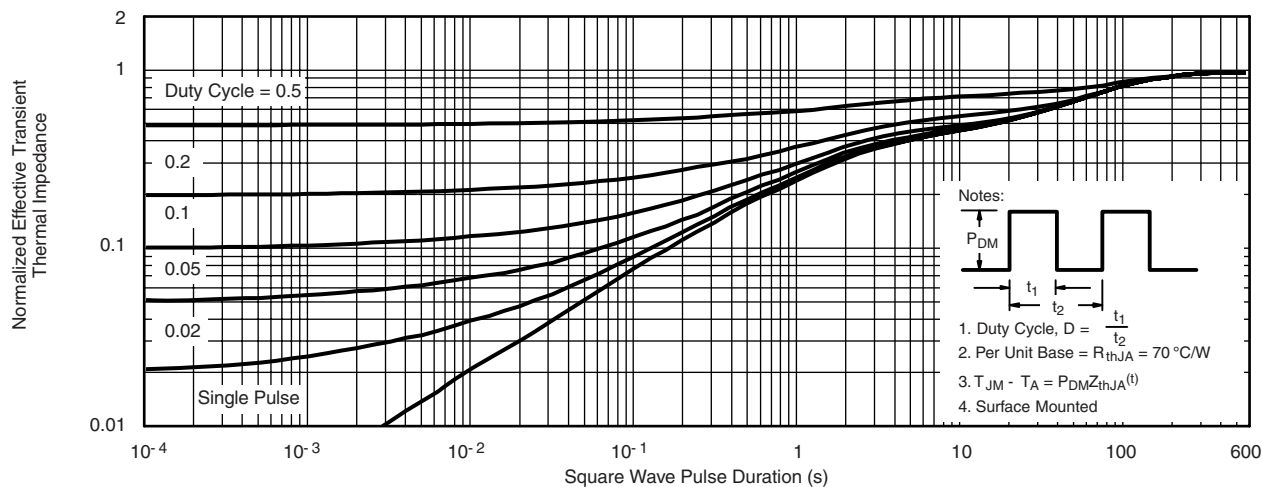
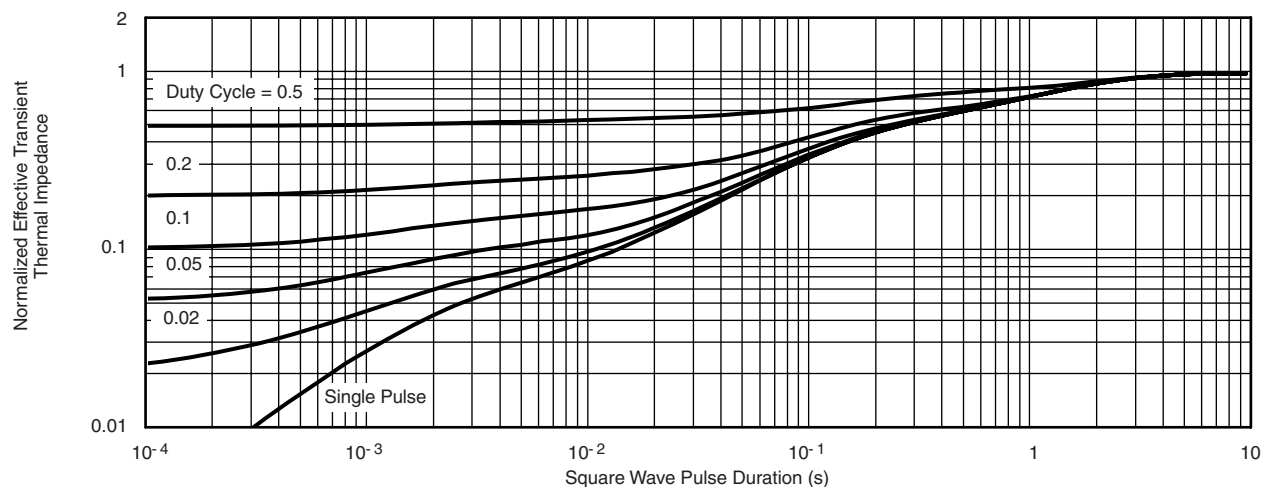
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

**TYPICAL CHARACTERISTICS** 25 °C unless otherwise noted**Reverse Current vs. Junction Temperature****Single Pulse Power****Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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